## AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## **Listing of Claims:**

1. (Previously Presented) A method of removing an oxide film on a surface of a substrate, comprising the steps of:

providing hydrogen radicals to the surface of the substrate;
providing fluorine radicals to the surface of the substrate; and
removing the oxide film by processing the surface of the substrate
with the hydrogen radicals and the fluorine radicals, wherein

the step of providing hydrogen radicals and the step of providing fluorine radicals are performed in parallel, and the step of providing hydrogen radicals is terminated after the step of providing fluorine radicals is terminated.

- 2. (Previously Presented) The method as claimed in claim 1, wherein the hydrogen radicals are generated by exciting hydrogen gas with high frequency plasma.
- 3. (Original) The method as claimed in claim 2, wherein the hydrogen radicals are generated outside a processing space in which the substrate is retained, and are transported to the processing space.
- 4. (Previously Presented) The method as claimed in claim 1, wherein the fluorine radicals are generated by exciting fluorine gas with ultra violet rays.
- 5. (Original) The method as claimed in claim 4, wherein the fluorine radicals are generated in a processing space in which the substrate is retained.
  - 6. (Cancelled)

7. (Previously Presented) The method as claimed in claim 1, wherein the step of providing the fluorine radicals is begun after the step of providing the hydrogen radicals is begun.

## 8. - 9. (Cancelled)

10. (Currently Amended) <u>A</u> The method as claimed in claim 9 of removing an oxide film on a surface of a substrate, comprising the steps of:

providing hydrogen radicals to the surface of the substrate;

providing fluorine radicals to the surface of the substrate;

providing water vapor to the surface of the substrate; and

removing the oxide film by processing the surface of the substrate with the hydrogen radicals and the fluorine radicals,

wherein

the step of providing hydrogen radicals and the step of providing fluorine radicals are performed in parallel; and

the step of providing hydrogen radicals and fluorine radicals in parallel and the step of providing water vapor are performed alternately and repeatedly.

11. (Previously Presented) The method as claimed in claim 10, wherein a processing space in which the substrate is retained is purged with inert gas after the step of providing water vapor and before the step of providing hydrogen radicals and fluorine radicals in parallel.

## 12. - 14. (Cancelled)